

Abstract of the Disclosure

Provided are a method of writing data into a memory cell with a boosted write voltage and a memory device that performs the method. The method involves (a) transmitting data input in response to a write command to a bitline; (b) writing the input
5 data on the bitline into a memory cell capacitor via a memory cell transistor; (c) generating a write boosting signal in response to the write command and a bitline precharge signal; (d) boosting a voltage of a capacitor connected between the write boosting signal and the bitline in response to the write boosting signal; (e) boosting a voltage of the bitline to a predetermined level; and (f) rewriting the input data into the
10 memory cell capacitor with the boosted voltage of the bitline.

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